VBJ1322 Datasheet

N-Channel 30 V (D-S) MOSFET

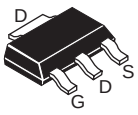
PRODUCT SUMMARY	
V_{DS} (V)	30
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.019
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.021
I_D (A)	7
Configuration	Single

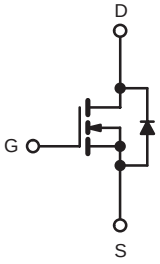
FEATURES

- Trench Power MOSFET
- 100 % R_g and UIS Tested

Pb-free
RoHS
COMPLIANT

SOT-223





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	T_C = 25 °C	I_D	7	A
	T_C = 125 °C		4.5	
Continuous Source Current (Diode Conduction)		I_S	5	
Pulsed Drain Current[a]		I_{DM}	31	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	10	
Single Pulse Avalanche Energy		E_{AS}	5	mJ
Maximum Power Dissipation[a]	T_C = 25 °C	P_D	4	W
	T_C = 125 °C		1.3	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount[b]	R_{thJA}	110	°C/W
Junction-to-Foot (Drain)		R_{thJF}	38	

Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. When mounted on 1" square PCB (FR-4 material).
c. Parametric verification ongoing.

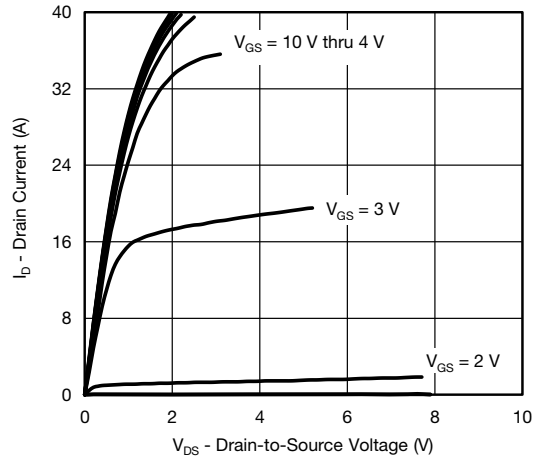
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA		30	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		0.5	-	1.5	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 30 V	-	-	1	µA
		V_{GS} = 0 V	V_{DS} = 30 V, T_J = 125 °C	-	-	50	
		V_{GS} = 0 V	V_{DS} = 30 V, T_J = 175 °C	-	-	150	
On-State Drain Current[a]	$I_{D(on)}$	V_{GS} = 10 V	V_{DS} ≥ 5 V	10	-	-	A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 6 A	-	0.019	-	Ω
		V_{GS} = 4.5 V	I_D = 4.9 A	-	0.021	-	
		V_{GS} = 10 V	I_D = 6 A, T_J = 125 °C	-	0.054	-	
		V_{GS} = 10 V	I_D = 6 A, T_J = 175 °C	-	0.064	-	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 5 A		-	21	-	S
Dynamic[b]							
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 15 V, f = 1 MHz	-	295	-	pF
Output Capacitance	C_{oss}			-	67	-	
Reverse Transfer Capacitance	C_{rss}			-	25	-	
Total Gate Charge[c]	Q_g	V_{GS} = 10 V	V_{DS} = 15 V, I_D = 6 A	-	6	-	nC
Gate-Source Charge[c]	Q_{gs}			-	1.2	-	
Gate-Drain Charge[c]	Q_{gd}			-	1	-	
Gate Resistance	R_g	f = 1 MHz		3.0	6.65	11	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 15 V, R_L = 2.5 Ω I_D ≅ 6 A, V_{GEN} = 10 V, R_g = 1 Ω		-	6	9	ns
Rise Time[c]	t_r			-	12	18	
Turn-Off Delay Time[c]	$t_{d(off)}$			-	13	20	
Fall Time[c]	t_f			-	8	12	
Source-Drain Diode Ratings and Characteristics[b]							
Pulsed Current[a]	I_{SM}			-	-	31	A
Forward Voltage	V_{SD}	I_F = 3 A, V_{GS} = 0 V		-	0.8	1.1	V

Notes

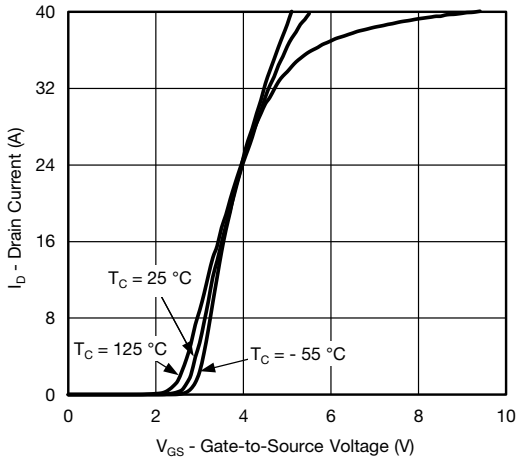
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

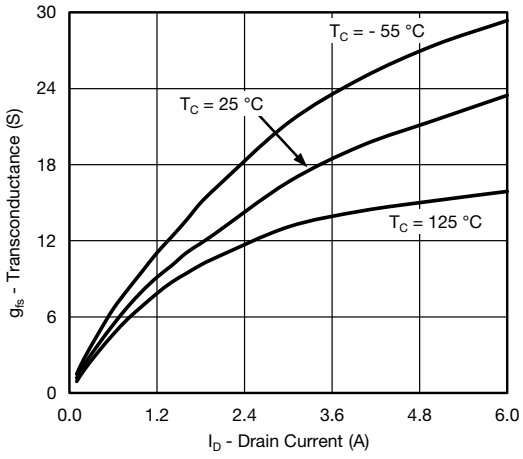
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



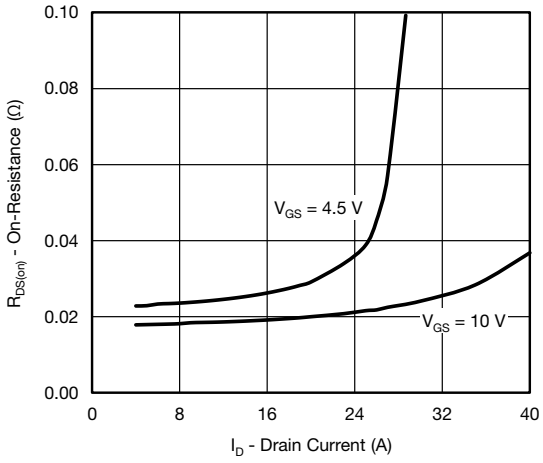
Output Characteristics



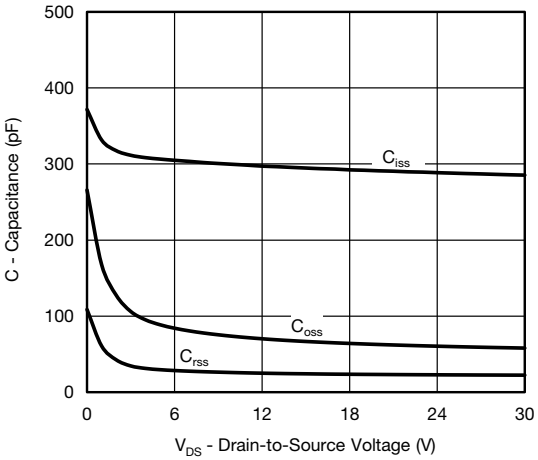
Transfer Characteristics



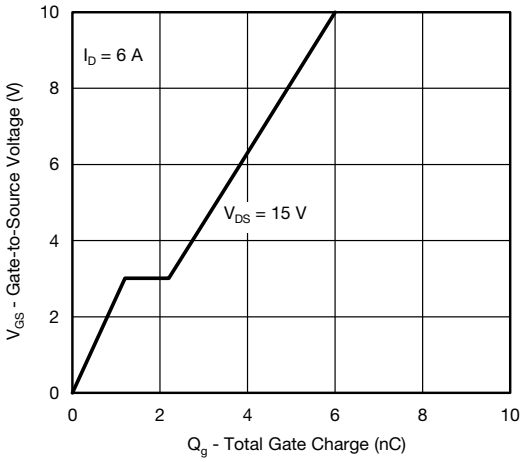
Transconductance



On-Resistance vs. Drain Current

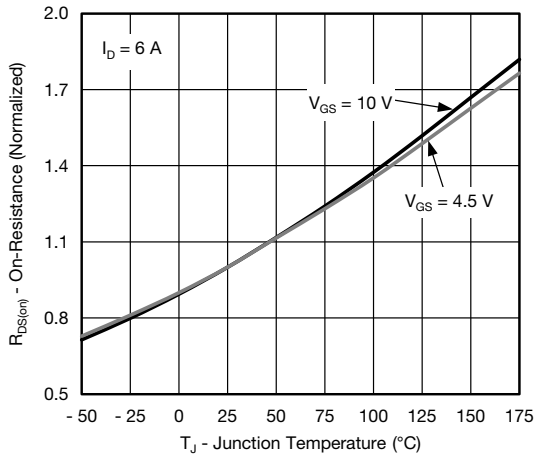


Capacitance

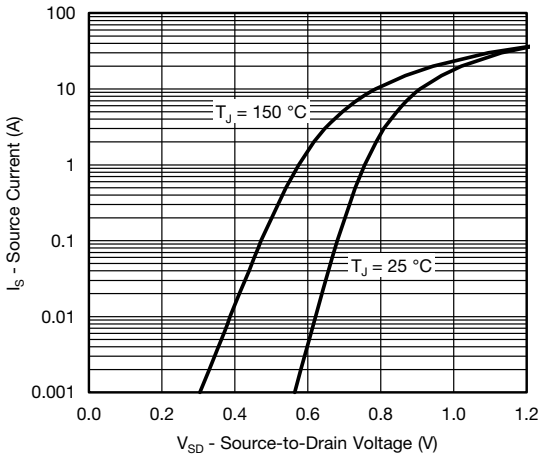


Gate Charge

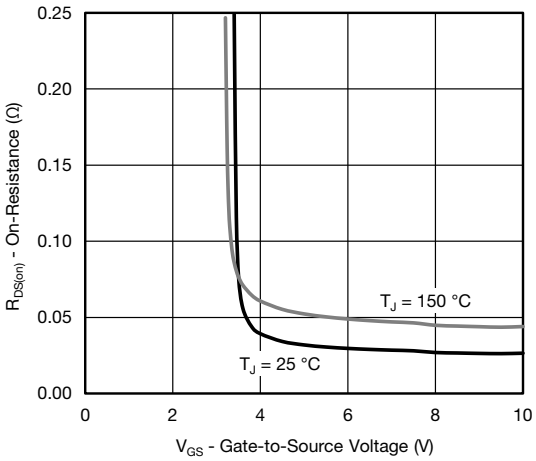
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



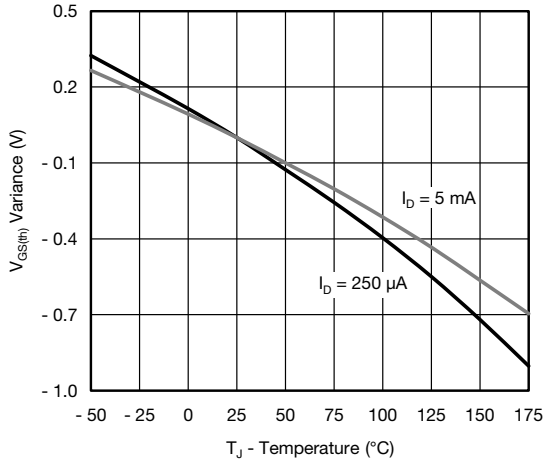
On-Resistance vs. Junction Temperature



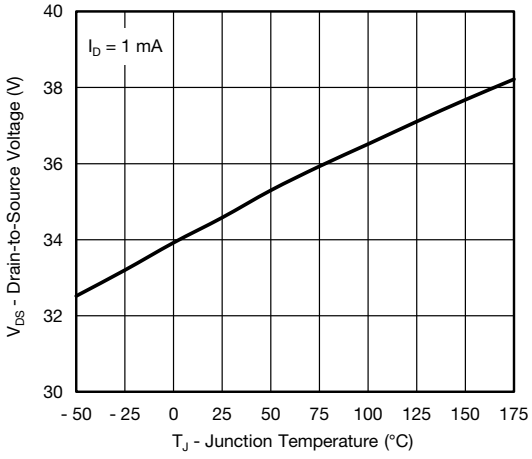
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

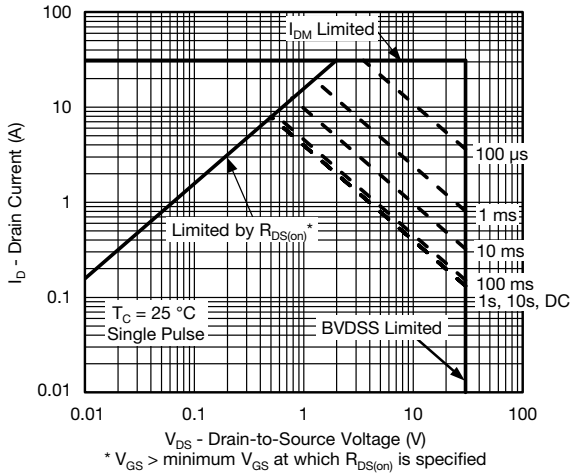


Threshold Voltage

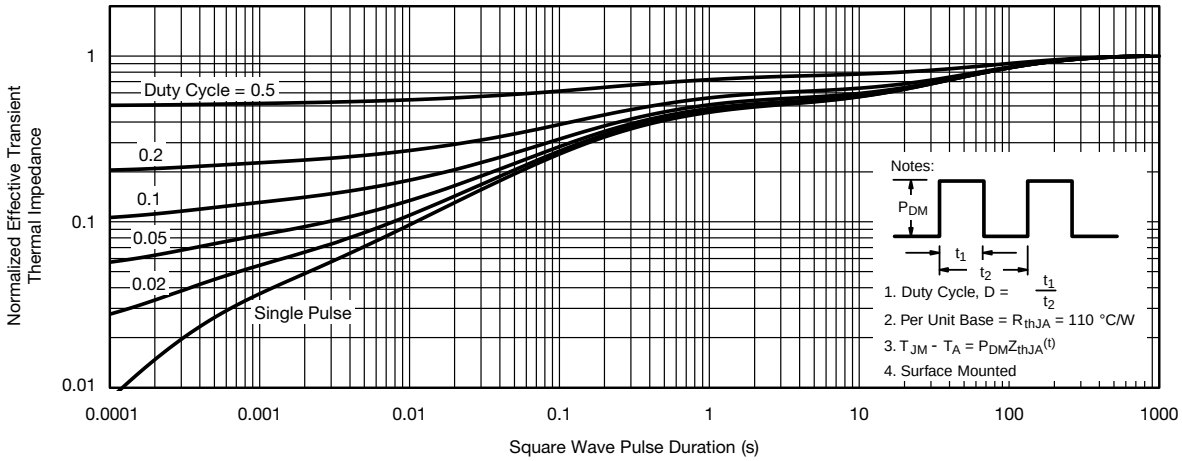


Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

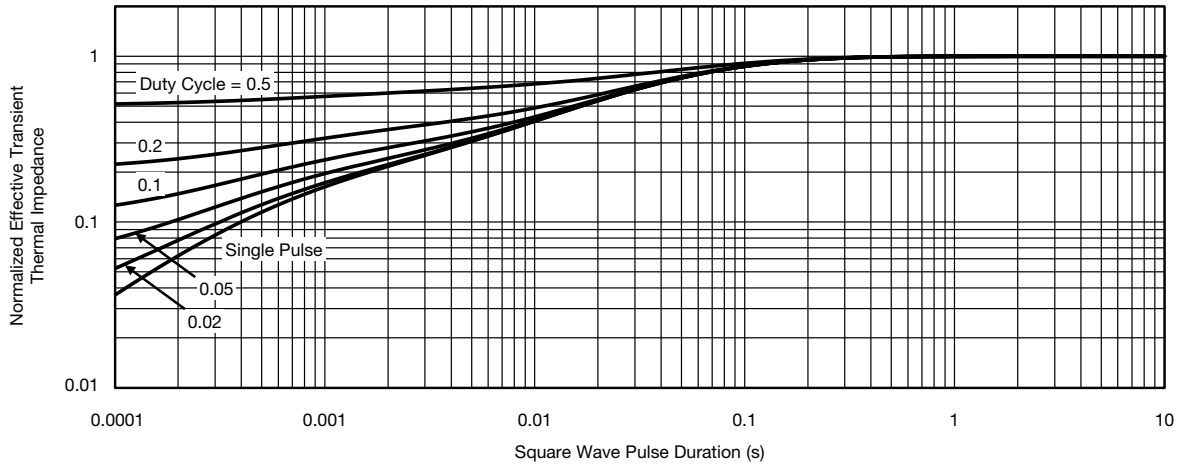


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



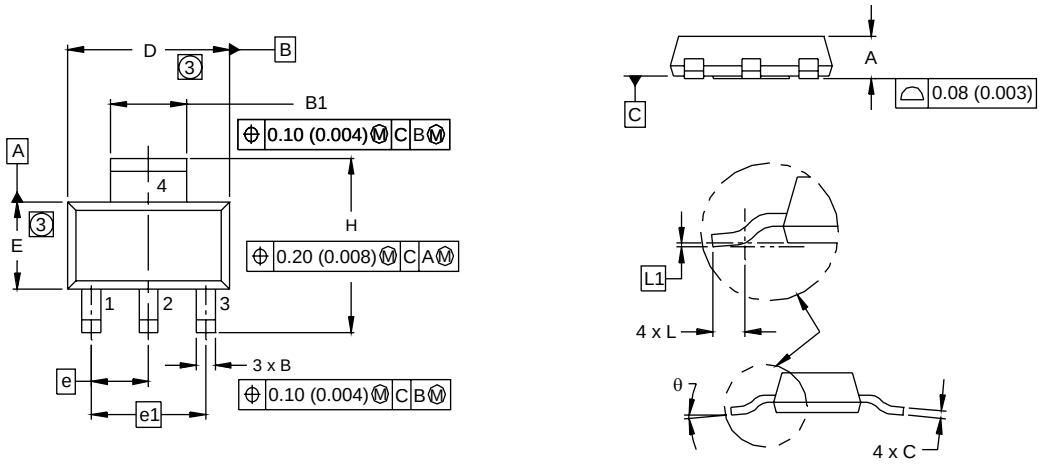
Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

SOT-223 (HIGH VOLTAGE)



	MILLIMETERS		INCHES	
DIM.	**MIN.**	**MAX.**	**MIN.**	**MAX.**
A	1.55	1.80	0.061	0.071
B	0.65	0.85	0.026	0.033
B1	2.95	3.15	0.116	0.124
C	0.25	0.35	0.010	0.014
D	6.30	6.70	0.248	0.264
E	3.30	3.70	0.130	0.146
e	2.30 BSC		0.0905 BSC	
e1	4.60 BSC		0.181 BSC	
H	6.71	7.29	0.264	0.287
L	0.91	-	0.036	-
L1	0.061 BSC		0.0024 BSC	
θ	-	10'	-	10'
ECN: S-82109-Rev. A, 15-Sep-08 DWG: 5969				

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension do not include mold flash.
4. Outline conforms to JEDEC outline TO-261AA.

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